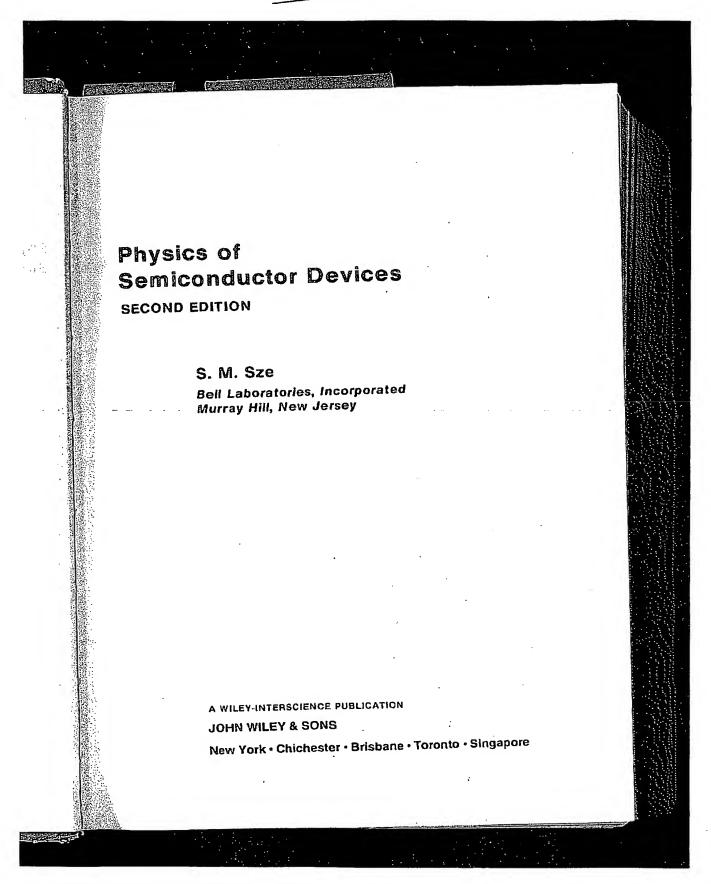
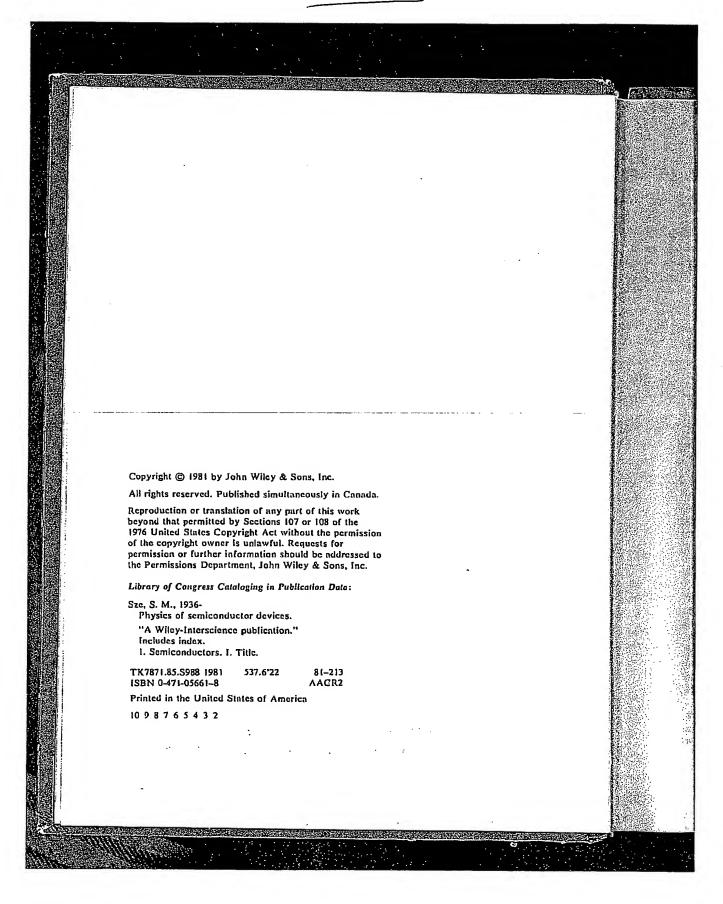
EXHIBIT 1 FOLLOWS THIS DIVIDER PAGE

Exhibit 1





Appendix I			
Properties of SiO ₂		•	
			eraj
and Si₃N₄ at 300 k		· •.	
		:	
Insulator:	SiO ₂	Si₃N₄	
Structure	Amorphous	Amorphous	
Melting point (°C)	~1600	*****	
Density (g/cm³)	2,2	3.1	
Refractive index	1.46	2.05	
Dielectric constant	3.9	7.5	
Dielectric strength (V/cm)	107	107	
Infrared absorption band (µm)	9.3	11.5-12.0	
Energy gap (eV)	9	~5.0	
Thermal-expansion coefficient (°C ⁻¹)	5×10 ⁻⁷		
Thermal conductivity (W/cm-K)	0.014		
dc resistivity (Ω-cm)			1 (4) 1 (3)
at 25°C	1014-1016	~1014	<i>₩</i>
at 500°C	1000	~2×10 ¹³ 5-10	
Etch rate in buffered HF ^a (Å/min)	1000	. 3-10	
*Buffered HF: 34.6% (wt.) NH ₄ F, 6.8% (wt.) HF, 58.6% H ₂ 0	D.	

EXHIBIT 2 FOLLOWS THIS DIVIDER PAGE